

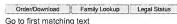


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Search scope: JP (bibliographic data only)

Years: 1991-2008

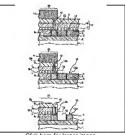
Patent/Publication No.: JP9107030



JP9107030 A METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE SHARP KK

Abstract:

PROBLEM TO BE SOLVED: To provide a method for manufacturing a semiconductor device which can effectively reduce electrostatic capacitance between wires when a multilaver wire structure is formed, in which mechanical strength of an upper layer wire can be enhanced. and in which reliability in elements cannot be damaged.



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SOLUTION: On an underlayer insulation film 2, with the use of resist 5 as a mask, in a region where a lower layer wire 10 does not exist out of an upper layer wire region 20, a silicon oxide film 6 is formed by a liquid phase growth method using a hydrogen silicon fluoride solution. Etching is performed until an upper face level of the lower layer wire 10. Thereon, a protection film 7 having a strength for the hydrogen silicon fluoride solution is formed, and successively a silicon oxide film 8 is formed by the liquid phase growth method using the hydrogen silicon fluoride solution. A metal film 9 is formed on an interlayer insulation film 18. With the use of resist 11, the metal film 9 is etched to form an upper layer wire, and also the interlayer insulation film 18 is etched to remove resist 5, 11.

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Current IPC-R:

	invention	additional
Advanced	H01L0021768 20060101	
	H01L0023522 20060101	
	invention	additional
Core	H01L002170 20060101	
	H01L002352 20060101	

Priority:

JP1995261530A 19951009

Patents Citing This One:

- ** US5930230 A 19990727 Qualcomm Incorporated
- ** US6424619 B2 20020723 Qualcomm Incorporated

No data available



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